

# 6-pin General purpose phototransistor Optocouplers

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**4N35**

## Description

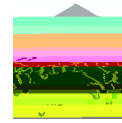
The general purpose optocouplers consist of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a standard plastic 6-pin dual-in-line package.

## Features

- Minimum Current Transfer Ratio at  $I_F = 10 \text{ mA}$ ,  $V_{CE} = 10 \text{ V}$ :
- 100% for 4N35
- Safety and Regulatory Approvals:
  - ◆ UL1577, 5,000 VAC<sub>RMS</sub> for 1 Minute
  - ◆ DIN-EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage (Pending)

## Applications

- Power Supply Regulators
- Digital Logic Inputs
- Microprocessor Inputs



PDIP6  
M TYPE  
CASE 646CG

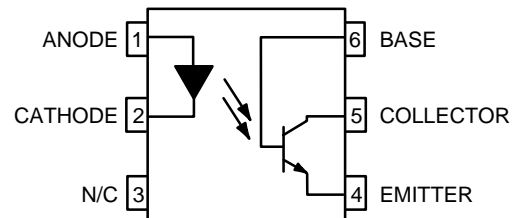
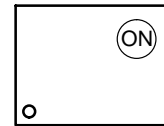


PDIP6  
STD TYPE  
CASE 646CU



PDIP6  
S TYPE  
CASE 646CV

## MARKING DIAGRAM



## ORDERING INFORMATION

this data sheet.

f

This document contains information on a product under development. onsemi reserves the right to change or discontinue this product without notice.

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**SAFETY AND INSULATION RATINGS** (As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for “safe electrical insulation” only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.)

Parameter		Characteristics
Installation Classifications per DIN VDE 0110/1.89 Table 1, For Rated Mains Voltage	<150 V <sub>RMS</sub>	I-IV

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## ELECTRICAL CHARACTERISTICS – INDIVIDUAL COMPONENT CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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### EMITTER

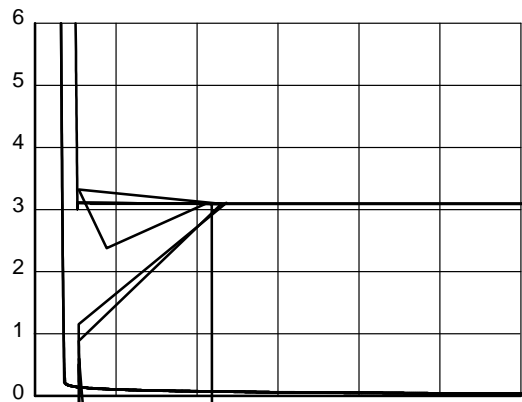
$V_F$	Input Forward Voltage	$I_F = 10 \text{ mA}$	–	1.20	1.50	V
$I_R$	Reverse Leakage Current	$V_R = 6.0 \text{ V}$	–	–	10	$\mu\text{A}$
$C_{in}$	Input Capacitance	$V = 0, f = 1 \text{ MHz}$	–	30	–	pF

### DETECTOR

$BV_{CEO}$	Collector-to-Emitter Breakdown Voltage	$I_C = 1.0 \text{ mA}, I_F = 0$	80	–	–	V
$BV_{CBO}$	Collector-to-Base Breakdown Voltage	$I_C = 0.1 \text{ mA}, I_F = 0$	80	–	–	V
$BV_{ECO}$	Emitter-to-Collector Breakdown Voltage	$I_E = 0.1 \text{ mA}, I_F = 0$	7	–	–	V
$BV_{EBO}$	Emitter-to-Base Breakdown Voltage	$I_E = 0.1 \text{ mA}, I_F = 0$	7	–	–	V

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## TYPICAL PERFORMANCE CURVES

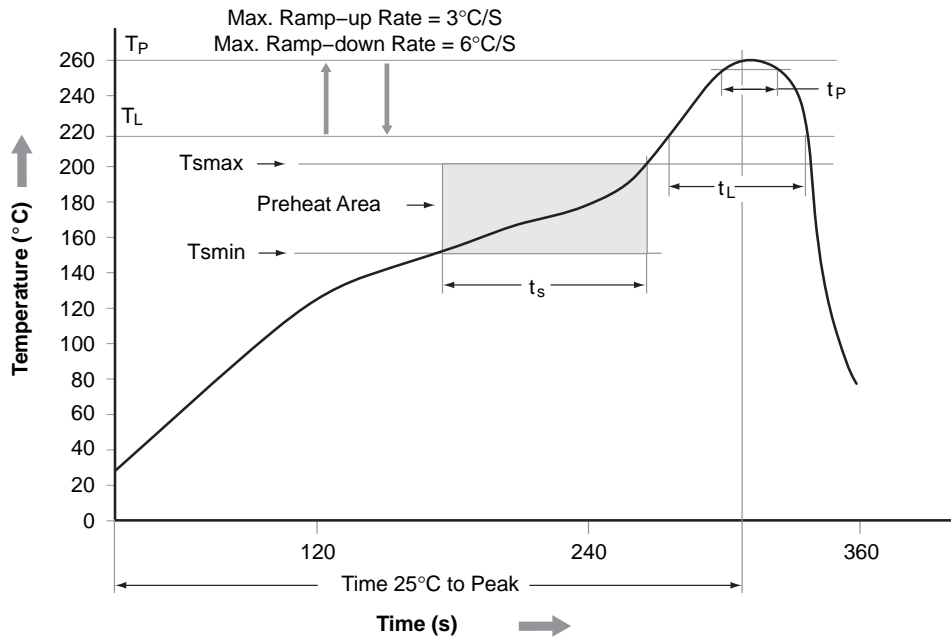






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## REFLOW PROFILE



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmín)	150°C
Temperature Max. (Tsmáx)	200°C
Time (ts) from (Tsmín to Tsmáx)	60–120 seconds
Ramp-up Rate (tL to tp)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / –5°C
Time (tp) within 5°C of 260°C	30 seconds
Ramp-down Rate (Tp to TL)	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

Figure 16. Reflow Profile

### ORDERING INFORMATION

Part Number	Package	Shipping†
4N35		

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## PACKAGE DIMENSIONS

PDIP6 7.12x6.50, 2.54P (M TYPE)

CASE 666CG

ISSUE 0042 Tw(M TYPE)



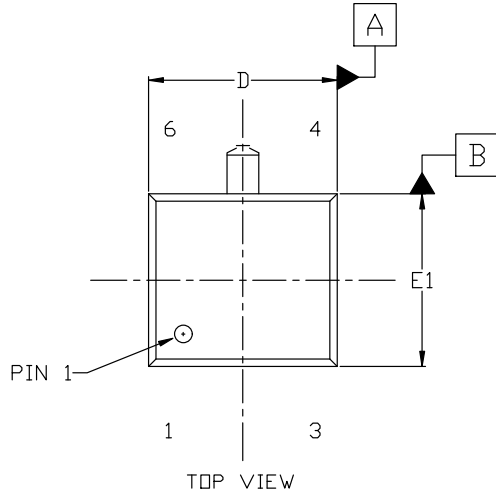
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## PACKAGE DIMENSIONS

PDIP6 7.12x6.50, 2.54P (STD TYPE)

CASE 646CU

ISSUE O



NOTES:

A) NO STANDARD A

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